

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(thickness and second conductivity-type semiconductor layers and crystalline semiconductor particles and equator and 40% and zenith region). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 13:57
L2	0	(crystalline semiconductor particles and indentation toward and the interior and surface below and equator).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 13:59
L3	0	(the second conductivity-type semiconductor layers and comprise and second impurity element selected and the group consisting of B P A1).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 14:01
L4	0	(the second conductivity-type semiconductor layers and comprise and second impurity element selected and the group consisting with B P A1). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 14:02
L5	0	(the second conductivity-type semiconductor layers and comprise and second impurity element selected and "group consisting" with "B P A1"). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 14:02
L6	0	(impurity element and concentrations of "5 x 10" and lower side and second conductivity-type semiconductor region and concentrations and "5 x 10" and upper side and second conductivity-type semiconductor region). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 14:05

S1	8	zenith and semiconductor particles	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S2	2	("6653552").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/24 09:24
S3	2	("6620996").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 06:38
S4	2	("4806495").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 06:39
S5	2	("4514580").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 06:39
S6	2	("4040867").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 11:03
S7	4	("4321416").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 11:03
S8	2	("5437735").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 11:04

S9	2	("5575861").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 11:04
S10	2	("5590495").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 11:05
S11	2	("20030217768").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/19 11:05
S12	0	(10/723953).OCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:28
S13	0	("10723953.AP").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:28
S14	0	("10723953.APP.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:29
S15	0	("723953.AP.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:29
S16	0	("857747.AP").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:29

S17	0	("911559.AP.").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:37
S18	2	("6071437").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:45
S19	2	("20010008143").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:46
S20	2	("6730840").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 09:56
S21	0	JP 2001-358351	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 09:56
S22	1	JP2001358351	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 09:57
S23	2	"2001358351"	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 10:30
S24	28	"3427200"	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 10:30

S25	4	("3427200").PN.	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:31
S26	125	particulate and sphere and p-type	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 13:25
S27	47	particulate and sphere and p-type and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 13:27
S28	2	particulate and sphere and p-type and (solar or photovoltaic) and surface roughness	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:22
S29	3	particulate and sphere and p-type and (solar or photovoltaic) and roughness	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 13:28
S30	47	particulate and sphere and p-type and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S31	365	sphere and p-type and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 13:28
S32	27	sphere and p-type and (solar or photovoltaic) and (surface roughness)	US_PGPUB; USPAT; USOCR; FFPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 14:25

S33	2	("4454372").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 14:26
S34	2	("4078944").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 14:26
S35	4	("3480818").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 14:26
S36	4	("3038952").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 15:33
S37	2	("4554727").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 15:35
S38	0	spheres and intrinsic and impurity and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 15:36
S39	162	spheres and intrinsic and impurity and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 15:41
S40	1	(sawtooth surface) and intrinsic and impurity and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 15:46

S41	2	(periodic reflective grating) and intrinsic and impurity and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 15:54
S42	0	(periodic reflective grating) and junction and impurity and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S43	2	(periodic reflective grating) and impurity and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 15:56
S44	0	(periodic reflective grating) and sphere and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 15:57
S45	10	(saw-tooth) and sphere and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 16:00
S46	334	(grating) and sphere and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 16:00
S47	64	(grating) and junction and sphere and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S48	0	(grating) and pin-junction and sphere and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 17:40

S49	3	pin-junction and sphere and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 17:41
S50	0	pin-junction and particulate and (solar or photovoltaic) and indentation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 17:41
S51	2	pin-junction and particulate and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 17:44
S52	23	pin-junction and particles and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 17:59
S53	2	("4260429").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 17:48
S54	2	("5084107").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 17:48
S55	0	pin-junction and texture particles and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 17:59
S56	4	pin-junction and texture and particles and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:00

S57	3	pin-junction and texture and sphere and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:01
S58	1	pin-junction and texture and particulate and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:02
S59	3	pin-junction and texture and sphere	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:02
S60	1	pin-junction and texture and particulate	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:03
S61	4	pin-junction and texture and particle	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:03
S62	15	pin-junction and textured	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:05
S63	3	pin-junction and indentation and particles	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:09
S64	3	pin-junction and indentation and sphere	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:09

S65	3	pin-junction and indentation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:09
S66	22	i-type and indentation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/23 18:09
S67	547	semiconductor and impurity and intrinsic and sphere	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 09:28
S68	1591	semiconductor and (impurity or concentration or gradient) and intrinsic and sphere	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 09:28
S69	616	semiconductor and ((impurity adj concentration) or gradient) and intrinsic and sphere	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 09:30
S70	8	semiconductor and ((impurity adj concentration) same gradient) and intrinsic and sphere	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 09:34
S71	2	("6653552").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/24 11:54
S72	0	("82788.AP.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/24 11:54

S73	4	"082788".AP.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 13:55
S74	616	lattice mismatch and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:24
S75	708	(n-type and impurity concentration) and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 15:54
S76	1	(n-type and impurity concentration decreasing) and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 15:55
S77	0	(n-type and i-type and impurity concentration decreasing) and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 15:56
S78	48	(n-type and i-type and impurity same decreasing) and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 16:15
S79	23135	Sugawara.IN.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:24
S80	135	Sugawara.IN. and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 16:15

S81	37	Sugawara,IN, and (solar or photovoltaic)and impurity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/24 17:38
S82	3	("4021323").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/24 17:38
S83	2	("4514580").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/24 19:38
S84	2	("6294822").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/30 13:29
S85	1	1999-190737.NRAN.	DERWENT	ADJ	ON	2007/07/30 13:30
S86	3	("4322571").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/30 13:37
S87	1	1999-190737.NRAN.	DERWENT	ADJ	ON	2007/07/30 13:37
S88	3	("4322571").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/08 09:52
S89	1726	((oxygen or nitrogen or carbon or hydrogen) same semiconduct\$3 layer) and (photovoltaic or solar)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:24
S90	80	((oxygen or nitrogen or carbon or hydrogen) same semiconduct\$3 particle) and (photovoltaic or solar)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 11:02

S91	2	("20030083544").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/08 14:17
S92	2	("20020023674").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/08 14:21
S93	2	("5,672,214").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/08 14:21
S94	3	particulate and sphere and p-type and (solar or photovoltaic) and surface roughness	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:22
S95	68	grating and junction and sphere and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S96	33243	particulate and sphere and p-type and solar or photovoltaic	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S97	52	particulate and sphere and p-type and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S98	0	(periodic reflective grating) and junction and impurity and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23

S99	9	zenith and semiconductor particle	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:23
S100	655	lattice mismatch and (solar or photovoltaic)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:24
S101	1726	((oxygen or nitrogen or carbon or hydrogen) same semiconductor\$3 layer) and (photovoltaic or solar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:24
S102	52	Sugawara.IN. and (solar or photovoltaic) and Particle	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:29
S103	10	(solar or photovoltaic) and oxygen with atoms/ cm3	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:32
S104	11	(solar or photovoltaic) and oxygen same atoms/ cm3	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:32
S105	8	(solar or photovoltaic) and (oxygen same atoms/ cm3 same concentration)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/08 14:33
S106	0	climax and semiconductor particles	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 11:39

S107	2	pinnacle and semiconductor particles	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 11:40
S108	87	(coat\$3 same particles same thickness same top) and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 11:41
S109	231	(coat\$3 same particles same thickness same side) and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 11:50
S110	23	(coat\$3 same particles same thickness same profile) and (solar or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 13:30
S111	499	(coat\$3 same particles same thickness same profile)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 13:33
S112	2118	(particles same thickness same profile)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 14:06
S113	13	Sugawara.IN. and (zenith)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 15:12
S114	459	Sugawara.IN. and (solar or photoelectric or photovoltaic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 15:42

S115	0	Shin Sugawara.IN. and (solar or photoelectric or photovoltaic)	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 15:43
S116	5	("1753721").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/01 17:11
S117	0	("10751833").PN.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/01 18:36
S118	0	"10751833"	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 18:36
S119	0	"10781355"	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 18:37
S120	1	"10/781355"	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 18:37
S121	0	(a second conductivity-type semiconductor region surrounding at least a part of the curved surface).clm.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/01 18:39
S122	1	(second conductivity and semiconductor layers and smaller thickness and equator and crystalline semiconductor particles and zenith).clm.	US_PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:30

S123	1	(second conductivity-type and semiconductor layers and smaller thickness and equator and crystalline semiconductor particles and zenith).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:31
S124	61	(thickness and second conductivity-type semiconductor layers and crystalline semiconductor particles and equator and 70% or less and zenith).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:32
S125	1	(thickness and second conductivity-type semiconductor layers and crystalline semiconductor particles and equator and 70% and less and zenith).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:33
S126	0	(thickness and each and second conductivity-type semiconductor layers and crystalline semiconductor particles and equator and 40% and zenith).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:35
S127	1	(crystalline semiconductor particles and indentation and interior and surface below and equator).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:37
S128	0	(second conductivity-type semiconductor layers and crystalline semiconductor particles and insulator layer and crystalline semiconductor particles and upper electrode layer and second conductivity-type semiconductor layers and second conductivity-type semiconductor layers and impurity element and concentration decreasing and proximity and crystalline semiconductor particles and the impurity element comprises and element selected and group consisting and nitrogen and carbon and hydrogen).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:41

S129	0	(second conductivity-type semiconductor layers and impurity element and concentration decreasing and proximity and crystalline semiconductor particles and the impurity element comprises and element selected and group consisting and nitrogen and carbon and hydrogen).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:42
S130	1	(second conductivity-type semiconductor layers and crystalline semiconductor particles and insulator layer and crystalline semiconductor particles and upper electrode layer and second conductivity-type semiconductor layers).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:43
S131	0	(second conductivity-type semiconductor layers and thickness and "not less than 5 nm" and "100" nm).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:44
S132	0	(photoelectric conversion device and region and second conductivity-type semiconductor layers and concentration of the impurity element and lowest comprises and intrinsic semiconductor).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:47
S133	0	("oxide layer or a nitride layer" with crystalline semiconductor particles with the second conductivity-type semiconductor layer).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/04/02 11:48

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